



ON Semiconductor®

# BS170 / MMBF170 N-Channel Enhancement Mode Field Effect Transistor

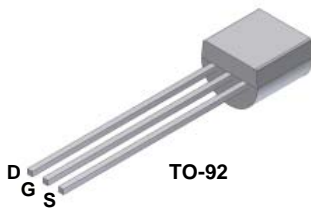
## General Description

These N-Channel enhancement mode field effect transistors are produced using ON Semiconductor's proprietary, high cell density, DMOS technology. These products have been designed to minimize on-state resistance while provide rugged, reliable, and fast switching performance. They can be used in most applications requiring up to 500mA DC. These products are particularly suited for low voltage, low current applications such as small servo motor control, power MOSFET gate drivers, and other switching applications.

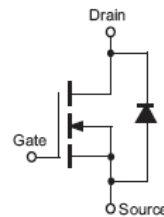
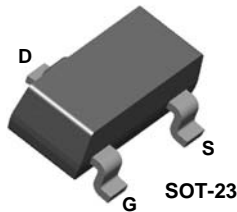
## Features

- High density cell design for low  $R_{DS(ON)}$ .
- Voltage controlled small signal switch.
- Rugged and reliable.
- High saturation current capability.

### BS170



### MMBF170



## Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
$V_{DSS}$	Drain-Source Voltage	60		V
$V_{DGR}$	Drain-Gate Voltage ( $R_{GS} \leq 1M\Omega$ )	60		V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$		V
$I_D$	Drain Current - Continuous - Pulsed	500	500	mA
		1200	800	
$T_J, T_{STG}$	Operating and Storage Temperature Range	- 55 to 150		$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering Purposes, 1/16" from Case for 10 Seconds	300		$^\circ\text{C}$

## Thermal Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	BS170	MMBF170	Units
$P_D$	Maximum Power Dissipation Derate above $25^\circ\text{C}$	830	300	mW
		6.6	2.4	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	150	417	$^\circ\text{C}/\text{W}$

**Electrical Characteristics**  $T_A=25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Conditions	Type	Min.	Typ.	Max.	Units
<b>OFF CHARACTERISTICS</b>							
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 100\mu A$	All	60			V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 25V, V_{GS} = 0V$	All			0.5	$\mu A$
$I_{GSSF}$	Gate - Body Leakage, Forward	$V_{GS} = 15V, V_{DS} = 0V$	All			10	nA
<b>ON CHARACTERISTICS (Notes 1)</b>							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 1mA$	All	0.8	2.1	3	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10V, I_D = 200mA$	All		1.2	5	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 10V, I_D = 200mA$	BS170		320		mS
		$V_{DS} \geq 2 V_{DS(on)}, I_D = 200mA$	MMBF170		320		
<b>Dynamic Characteristics</b>							
$C_{iss}$	Input Capacitance	$V_{DS} = 10V, V_{GS} = 0V, f = 1.0MHz$	All		24	40	pF
$C_{oss}$	Output Capacitance		All		17	30	pF
$C_{rss}$	Reverse Transfer Capacitance		All		7	10	pF
<b>Switching Characteristics (Notes 1)</b>							
$t_{on}$	Turn-On Time	$V_{DD} = 25V, I_D = 200mA, V_{GS} = 10V, R_{GEN} = 25\Omega$	BS170			10	ns
		$V_{DD} = 25V, I_D = 500mA, V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	
$t_{off}$	Turn-Off Time	$V_{DD} = 25V, I_D = 200mA, V_{GS} = 10V, R_{GEN} = 25\Omega$	BS170			10	ns
		$V_{DD} = 25V, I_D = 500mA, V_{GS} = 10V, R_{GEN} = 50\Omega$	MMBF170			10	

**Note:**

1. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2.0\%$ .

**Ordering Information**

Part Number	Package	Package Type	Lead Frame	Pin array
BS170	TO-92	BULK	STRAIGHT	D G S
BS170-D26Z	TO-92	Tape and Reel	FORMING	D G S
BS170-D27Z	TO-92	Tape and Reel	FORMING	D G S
BS170-D74Z	TO-92	AMMO	FORMING	D G S
BS170-D75Z	TO-92	AMMO	FORMING	D G S
MMBF170	SOT-23	Tape and Reel		

## Typical Electrical Characteristics

BS170 / MMBF170

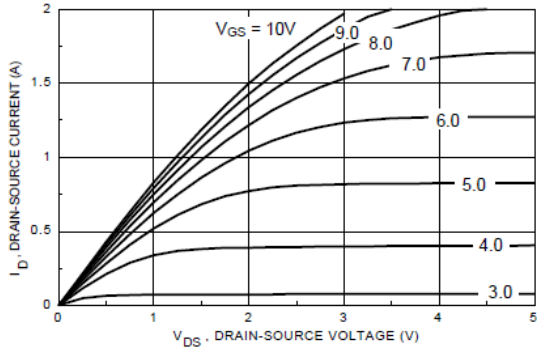


Figure 1. On-Region Characteristics.

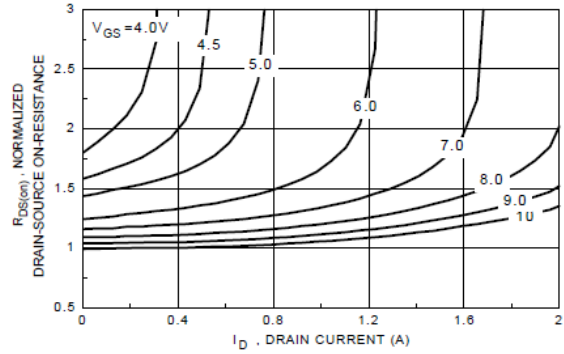


Figure 2. On-Resistance Variation with Gate Voltage and Drain Current.

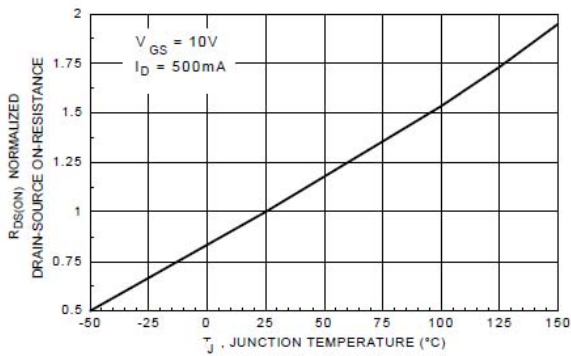


Figure 3. On-Resistance Variation with Temperature.

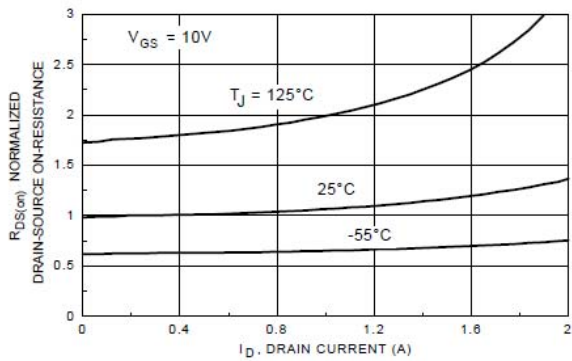


Figure 4. On-Resistance Variation with Drain Current and Temperature.

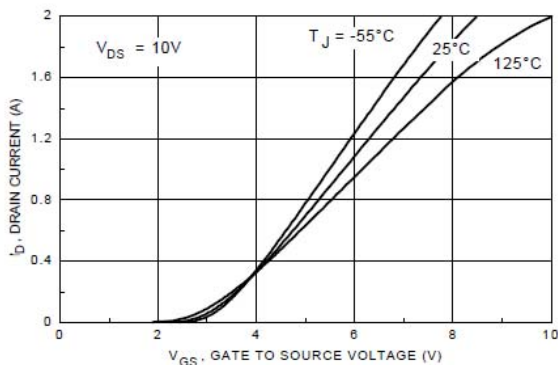


Figure 5. Transfer Characteristics.

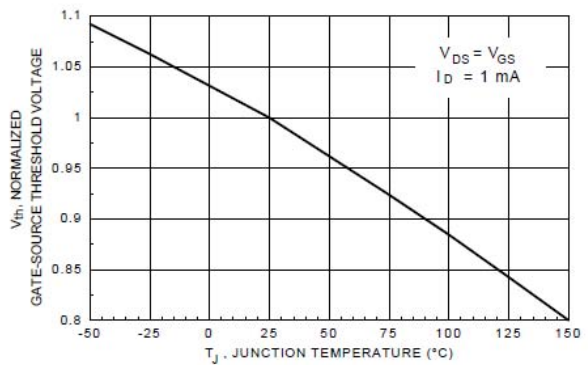


Figure 6. Gate Threshold Variation with Temperature.

Typical Electrical Characteristics (continued)

BS170 / MMBF170

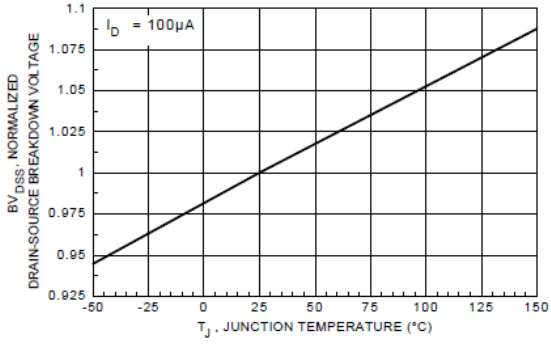


Figure 7. Breakdown Voltage Variation with Temperature.

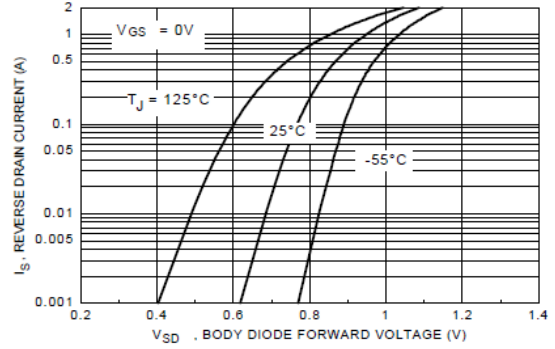


Figure 8. Body Diode Forward Voltage Variation with Current and Temperature.

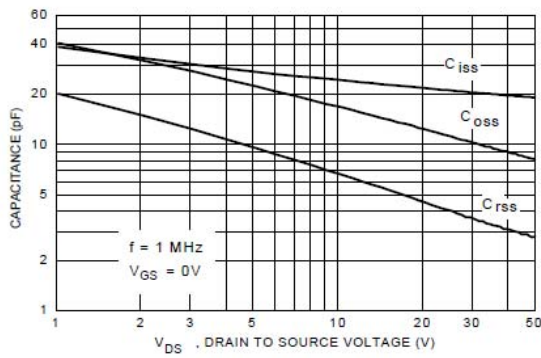


Figure 9. Capacitance Characteristics.

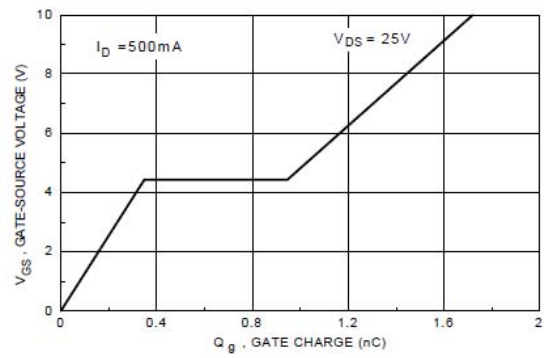


Figure 10. Gate Charge Characteristics.

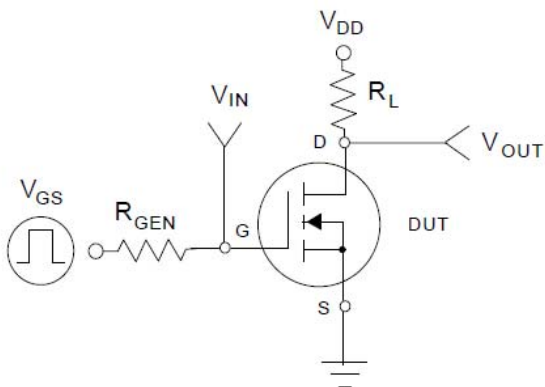


Figure 11. Switching Test Circuit.

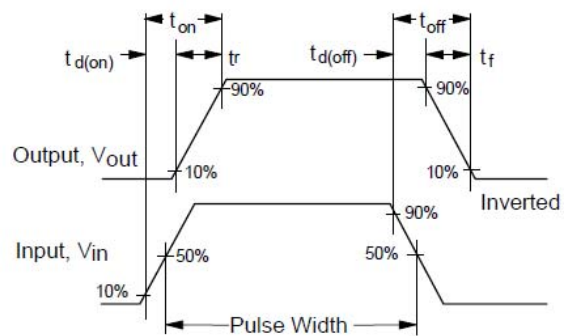


Figure 12. Switching Waveforms.

Typical Electrical Characteristics (continued)

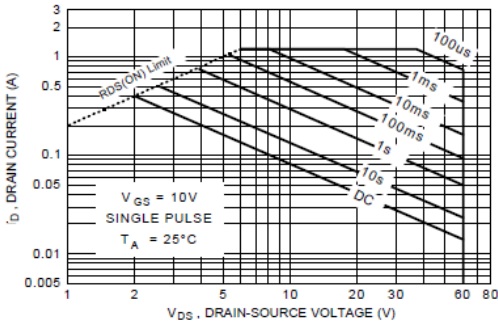


Figure 13. BS170 Maximum Safe Operating Area.

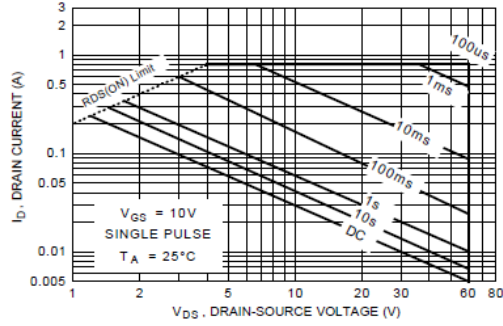


Figure 14. MMBF170 Maximum Safe Operating Area.

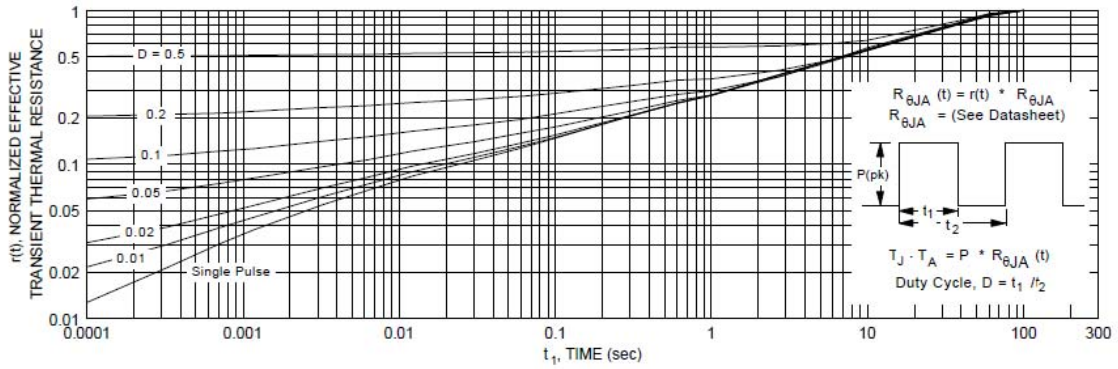


Figure 15. TO-92, BS170 Transient Thermal Response Curve.

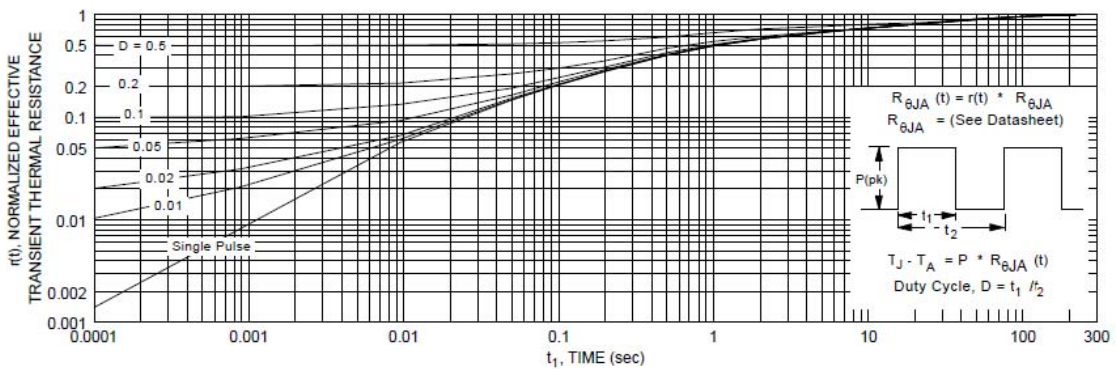


Figure 16. SOT-23, MMBF170 Transient Thermal Response Curve.



## TO-92 Tape and Reel Data, continued

### TO-92 Packing




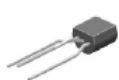

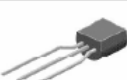
Information: Figure 2.0

TO-92 TNR/AMMO PACKING INFORMATION TABLE

Packing	Style	Quantity	EOL code
Reel	A	2,000	D26Z
	B	2,000	D11Z
	C	2,000	D28Z
	D	2,000	D10Z
	E	2,000	D27Z
	F	2,000	D81Z
	G	2,000	D29Z
	H	2,000	D89Z
Ammo	M	2,000	D74Z
	P	2,000	D75Z

Unit weight = 0.22 gm  
 Reel weight with components = 1.04 kg  
 Ammo weight with components = 1.02 kg  
 Max quantity per intermediate box = 10,000 units

TO-92 BULK PACKING INFORMATION TABLE

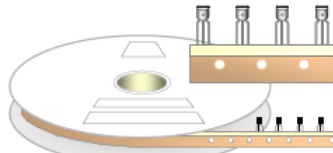
EOL CODE / FLOW OPTION	DESCRIPTION	LEADCLIP DIMENSION	MINIMUM ORDER QTY	LEADFORM OUTLINE
NO EOL CODE	STRAIGHT LEADS	NO LEAD CLIP	2.0K / BOX	
J18Z	TO-18 OPTION STD	NO LEAD CLIP	2.0K / BOX	
J35Z	TO-18 OPTION REVERSE	NO LEAD CLIP	2.0K / BOX	
J05Z	TO-5 OPTION STD	NO LEAD CLIP	1.5K / BOX	
J60Z	TO-5 OPTION REVERSE	NO LEAD CLIP	1.5K / BOX	
J61Z	IN LINE 0.200 SPACING	NO LEAD CLIP	1.5K / BOX	

TO-92 Tape and Reel Data, continued

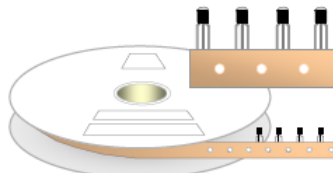
TO-92 Reeling Style

Configuration: Figure 3.0

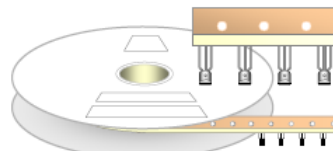
Machine Option "A" (H)



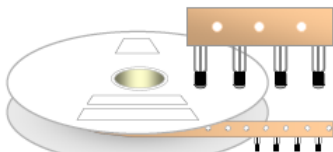
Style "A", D26Z



Style "B", D11Z

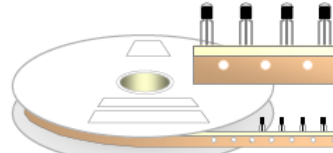


Style "C", D28Z

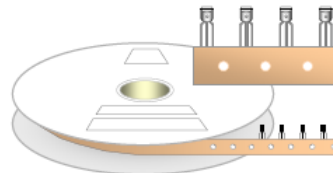


Style "D", D10Z

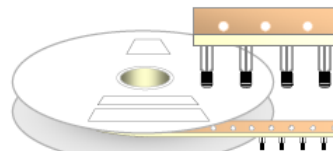
Machine Option "E" (J)



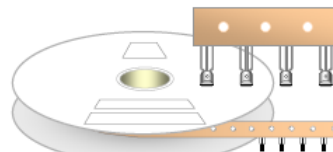
Style "E", D27Z



Style "F", D81Z



Style "G", D29Z

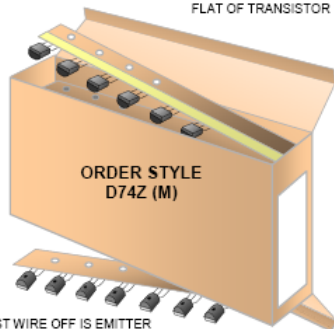


Style "H", D89Z

TO-92 Radial Ammo Packaging

Configuration: Figure 4.0

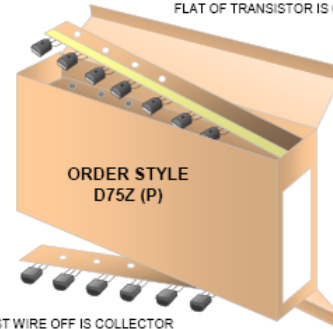
FIRST WIRE OFF IS COLLECTOR  
ADHESIVE TAPE IS ON THE TOP SIDE  
FLAT OF TRANSISTOR IS ON TOP



ORDER STYLE  
D74Z (M)

FIRST WIRE OFF IS EMITTER  
ADHESIVE TAPE IS ON BOTTOM SIDE  
FLAT OF TRANSISTOR IS ON BOTTOM

FIRST WIRE OFF IS EMITTER  
ADHESIVE TAPE IS ON THE TOP SIDE  
FLAT OF TRANSISTOR IS ON BOTTOM



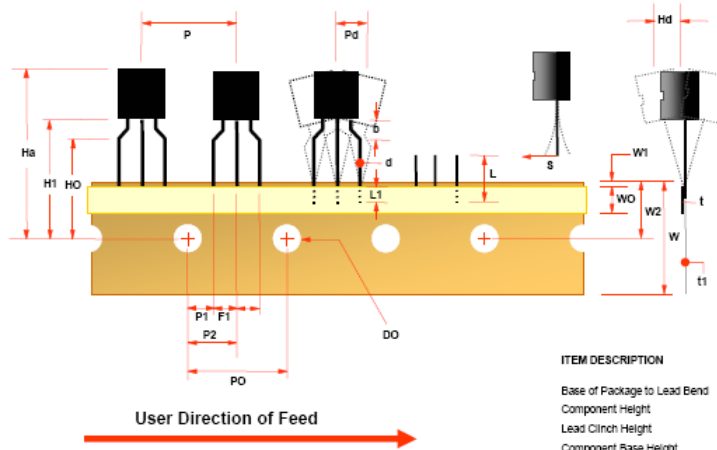
ORDER STYLE  
D75Z (P)

FIRST WIRE OFF IS COLLECTOR  
ADHESIVE TAPE IS ON BOTTOM SIDE  
FLAT OF TRANSISTOR IS ON TOP



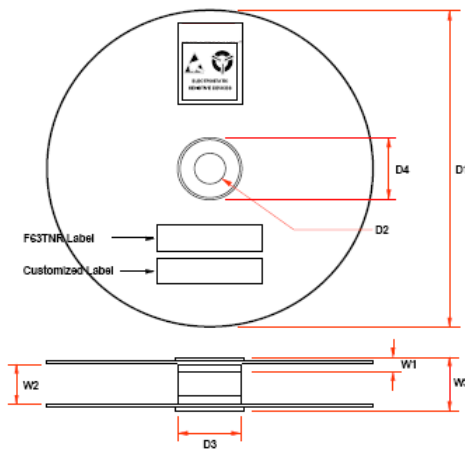
## TO-92 Tape and Reel Data, continued

### TO-92 Tape and Reel Taping Dimension Configuration: Figure 5.0



ITEM DESCRIPTION	SYMBOL	DIMENSION
Base of Package to Lead Bend	b	0.098 (max)
Component Height	Ha	0.929 (+/- 0.025)
Lead Clinch Height	HO	0.630 (+/- 0.020)
Component Base Height	H1	0.748 (+/- 0.020)
Component Alignment ( side/side )	Pd	0.040 (max)
Component Alignment ( front/back )	Hd	0.031 (max)
Component Pitch	P	0.500 (+/- 0.020)
Feed Hole Pitch	PO	0.500 (+/- 0.008)
Hole Center to First Lead	P1	0.150 (+0.009, -0.010)
Hole Center to Component Center	P2	0.247 (+/- 0.007)
Lead Spread	F1/F2	0.104 (+/- 0.010)
Lead Thickness	d	0.018 (+0.002, -0.003)
Cut Lead Length	L	0.429 (max)
Taped Lead Length	L1	0.209 (+0.051, -0.052)
Taped Lead Thickness	t	0.032 (+/- 0.006)
Carrier Tape Thickness	t1	0.021 (+/- 0.006)
Carrier Tape Width	W	0.708 (+0.020, -0.019)
Hold - down Tape Width	WO	0.236 (+/- 0.012)
Hold - down Tape position	W1	0.035 (max)
Feed Hole Position	W2	0.360 (+/- 0.025)
Sprocket Hole Diameter	DO	0.157 (+0.008, -0.007)
Lead Spring Out	S	0.004 (max)

### TO-92 Reel Configuration: Figure 6.0



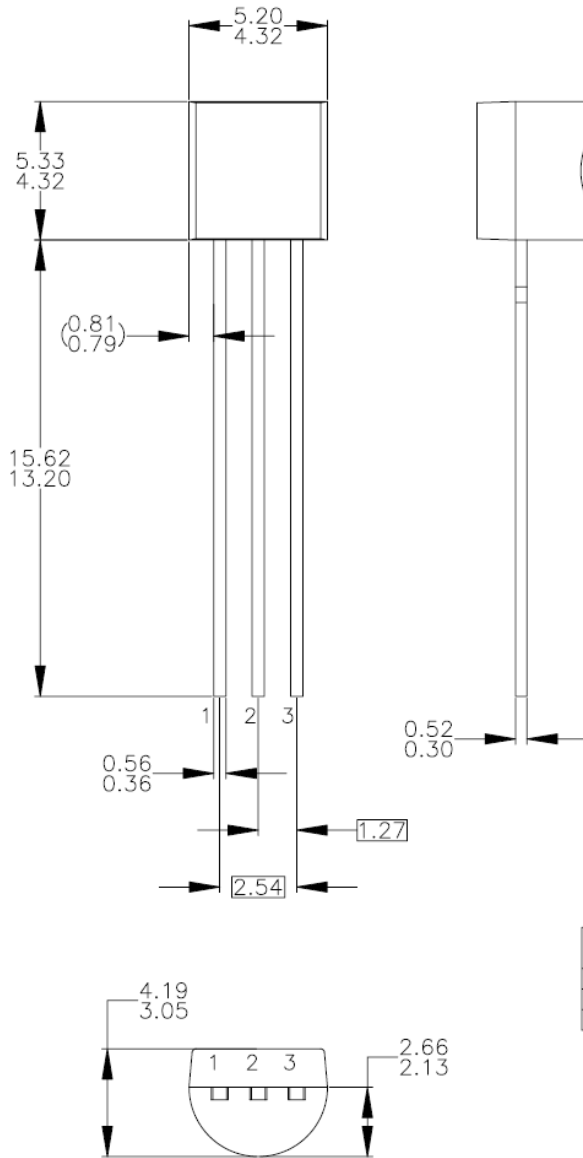
Note : All dimensions are in inches.

ITEM DESCRIPTION	SYMBOL	MINIMUM	MAXIMUM
Reel Diameter	D1	13.975	14.025
Arbor Hole Diameter (Standard)	D2	1.160	1.200
(Small Hole)	D2	0.650	0.700
Core Diameter	D3	3.100	3.300
Hub Recess Inner Diameter	D4	2.700	3.100
Hub Recess Depth	W1	0.370	0.570
Flange to Flange Inner Width	W2	1.630	1.690
Hub to Hub Center Width	W3		2.090

Note: All dimensions are inches

Mechanical Dimensions ( TO-92 )

TO-92



NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-1994.
- D) TO-92 (92,94,96,97,98) PIN CONFIGURATION:

PIN	92			94			96			97			98		
	P	F	M	P	F	M	P	F	M	P	F	M	P	F	M
1	E	S	S	E	S	S	B	D	G	C	G	D	C	G	D
2	B	D	G	C	G	D	E	S	S	B	D	G	E	S	S
3	C	G	D	B	D	G	C	G	D	E	S	S	B	D	G

LEGEND:

P - BIPOLAR      E - EMITTER      D - DRAIN  
 F - JFET          B - BASE            S - SOURCE  
 M - DMOS        C - COLLECTOR      G - GATE

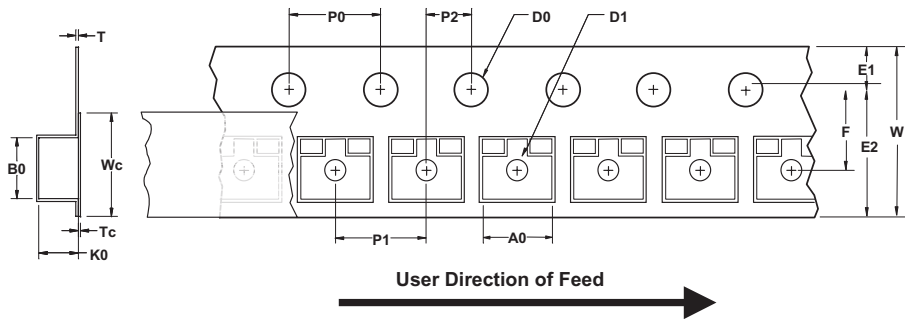
- E) FOR PACKAGE 92, 94, 96, 97 AND 98: PIN CONFIGURATION DRAIN "D" AND SOURCE "S" ARE INTERCHANGEABLE AT JFET "F" OPTION.
- F) DRAWING FILENAME: MKT-2A03DREV3.

Dimensions in Millimeters



## SOT-23 Std Tape and Reel Data, continued

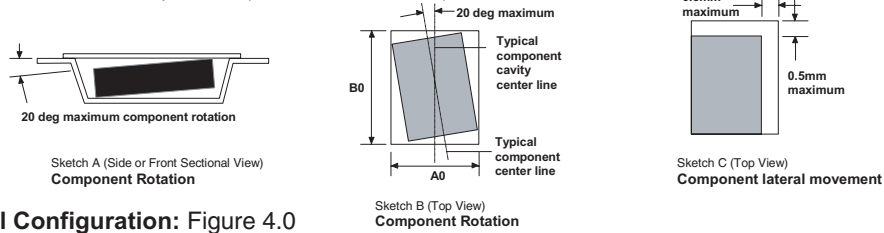
### SOT23-3L Embossed Carrier Tape Configuration: Figure 3.0



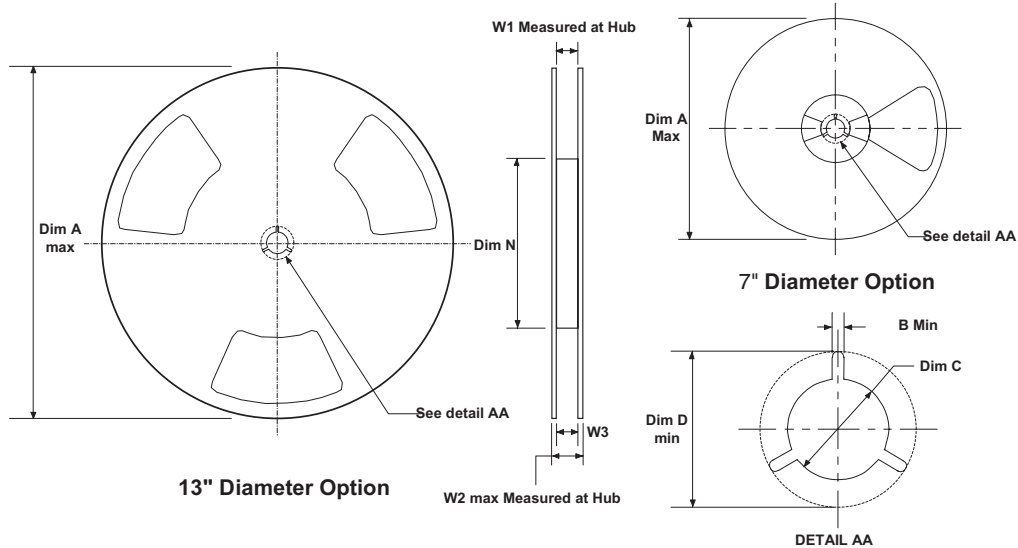
Dimensions are in millimeter

Pkg type	A0	B0	W	D0	D1	E1	E2	F	P1	P0	K0	T	Wc	Tc
SOT-23 (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



### SOT23-3L Reel Configuration: Figure 4.0

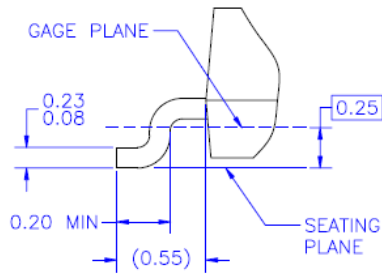
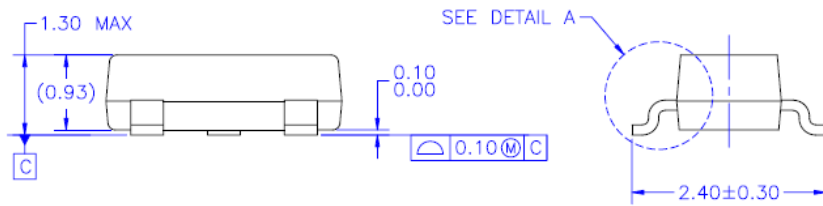
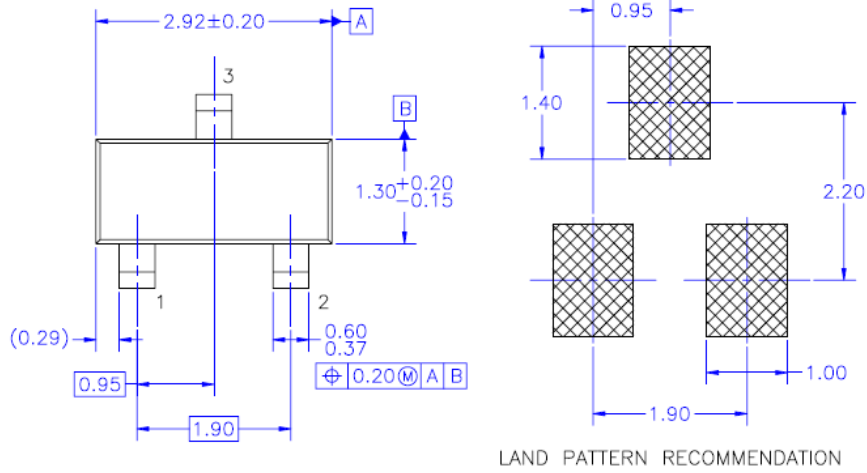


Dimensions are in inches and millimeters

Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9

**Mechanical Dimensions ( SOT-23 )**

**SOT-23**




DETAIL A  
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M — 1994.
- E) DRAWING FILE NAME: MA03DREV9

Dimensions in Millimeters

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